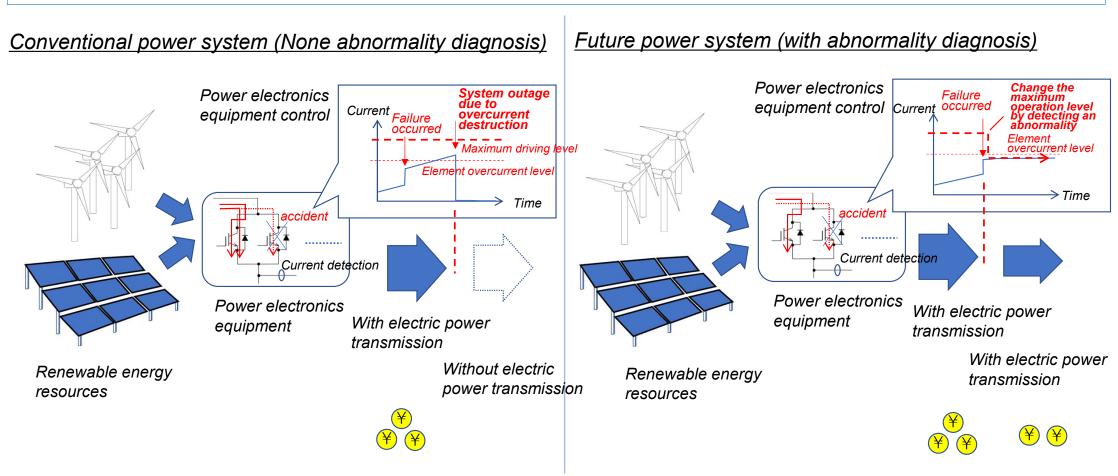
3. Research on abnormality diagnosis technology for power electronics equipment using machine learning

①王, 中嶋, 原田, 浦壁,

「機械学習によるDC/DCコンバータの異常診断」, 令和4年電気学会全国大会, WEB15-A3 パワーエレクトロニクス DC-DC変換(非絶縁) 4-038 (2022)

②王,原田,浦壁,

「機械学習を活用したDC/DCコンバータの異常診断技術の検討」, 電気学会研究会資料(半導体電力変換/モータドライブ合同研究会), SPC-23-023/MD-23-023 (2023) Purpose: Realization of abnormality diagnosis technology for power electronics equipment utilizing machine learning that does not require deep specialized knowledge or the addition of many measuring instruments with the aim of improving the continuity of operation of electric power and mobile equipment.



Advantages of abnormality diagnosis function + power electronics control

1. Using the machine learning method SVM, the diagnosis of abnormalities in DC/DC converter components is verified by simulation. Four states are identified using output voltage waveform data with time resolution of 80k~800kHz (5) and voltage resolution of 8~14bit (7).

(1)Verification conditions

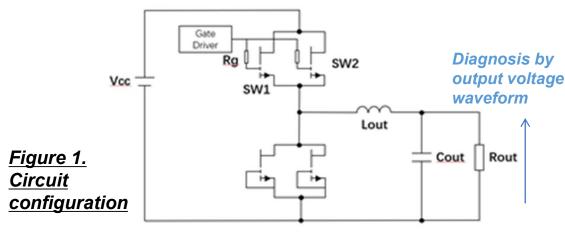


Table 1. Circuit parameters for the four states

	SW	Lout	Cout
All normal	SW1: Action SW2: Action	800 µH±5 %	0.47 μF±5 %
Only SW is abnormal	SW1: Action SW2: Stop	Normal	Normal
Only Lout is abnormal	Normal	800 μH -50 % ~ -6 % +6 % ~ +10 %	Normal
Only Cout is abnormal	Normal	Normal	0.47 μF -50 % ~ -6% +6 % ~ +10%

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	Steady-state waveform	Transient state waveform				
Vcc	400V±5%					
SW1, SW2	GaN HEMT GS66516B model					
Rg	2Ω±5%					
Rout	20Ω±5% (Load)	$1k\Omega \pm 5\%$ (Resistance to discharge)				
SW frequency•Duty• Gate Voltage	80kHz,Duty50% Vgs=6V	80kHz,Duty10% Vgs=6V				
The number of data	4000 (Teacher 3200/Examination 800)					

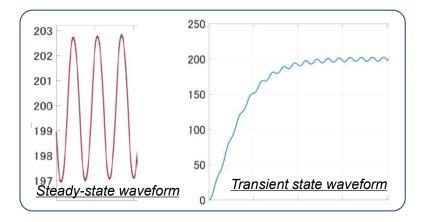
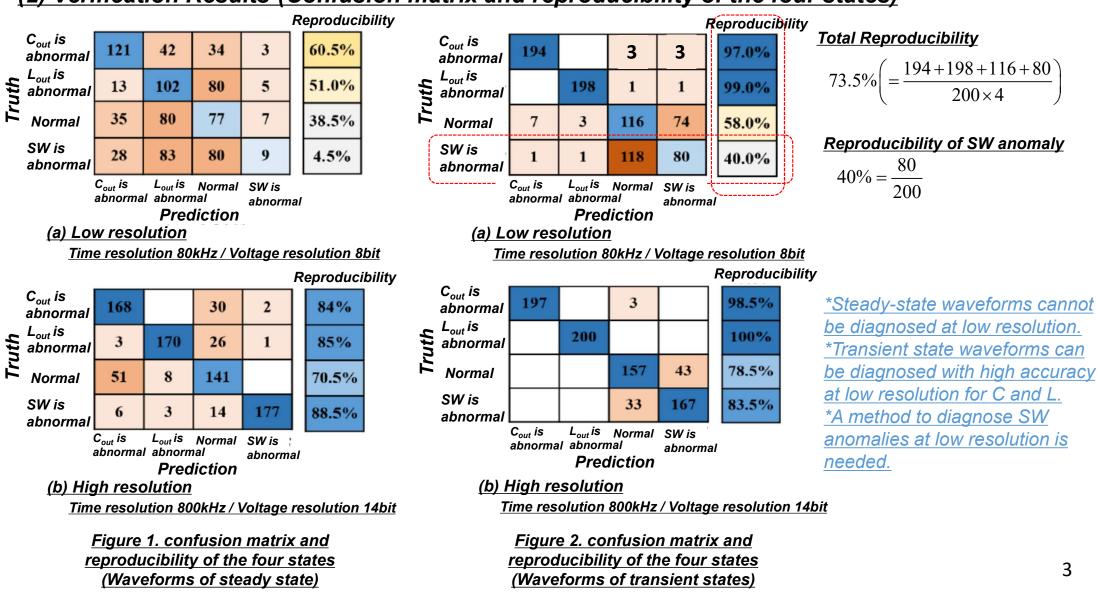


Table 2. Other circuit parameters

2



(2) Verification Results (Confusion matrix and reproducibility of the four states)

2. Using the machine learning method SVM, the diagnosis of abnormalities in DC/DC converter components is verified by simulation. We propose a method with high discrimination accuracy under low detection resolution conditions.

(1) Verification conditions

- ①Simulation circuit: Same as 1.(1)
- ②Four conditions to diagnose: Same as 1.(1)
- ③Diagnostic waveform:
- Output voltage in transient state ④ Other conditions

Vcc	400V±5%		
SW1, SW2	GaN HEMT GS66516Bのモデル		
Rg	2Ω±5%		
Rout	1kΩ±5%(放電抵抗)		
ゲート信号	80kHz,Duty10% <u>Vgs=1.5V</u>		
分解能毎の 波形の数	4000(教師3200/試験800)		

(2) Verification results (Total reproduction rate for <u>4 conditions)</u>

	80kHz (1 ^(*2))	160kHz (2)	240kHz (3)	400kHz (5)	800kHz (10)
8bit(391mV ^(*1))	98.8%	99.0%	98.6%	98.4%	99.4%
9bit(195mV)	98.9%	99.4%	99.3%	99.3%	98.1%
10bit(98mV)	99.3%	99.5%	99.6%	99.4%	99.0%
11bit(49mV)	99.8%	99.5%	99.5%	99.8%	99.5%
12bit(24mV)	99.4%	99.5%	99.9%	99.3%	99.3%
13bit(12mV)	99.6%	99.5%	99.5%	99.5%	99.4%
14bit(6mV)	99.8%	99.5%	99.5%	97.6%	99.6%

(*1) Voltage for 1 bit

(*2) Ratio to carrier frequency

<u>*Highly accurate diagnosis is possible by setting the transient state waveform and gate drive voltage</u> to 1.5V (near threshold).